



Single Pulse Avalanche Energy (L=0.1mH,VGS=10V,Rg=25 -	E_{AS}	180	mJ
---	----------	-----	----

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	40	° C/W
Soldering temperature, wave soldering for 10s	T_{sold}	-	-	265	° C

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA

St12 493.799.19 154.37 53.76 r



Fig.7 Gate Charge Characteristics

Fig.8 Capacitance vs Vds

Fig.



Fig.17 Avalanche Measurement Circuit

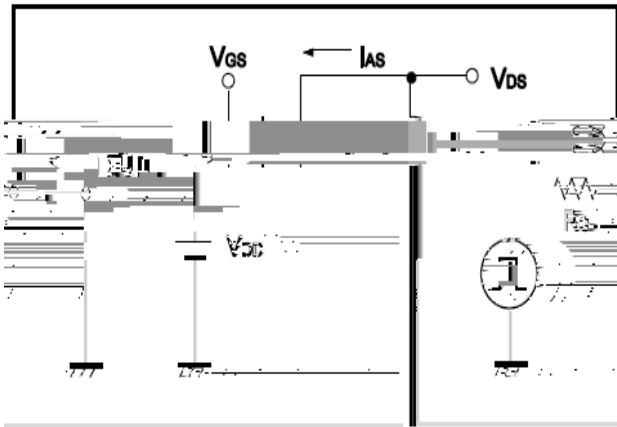
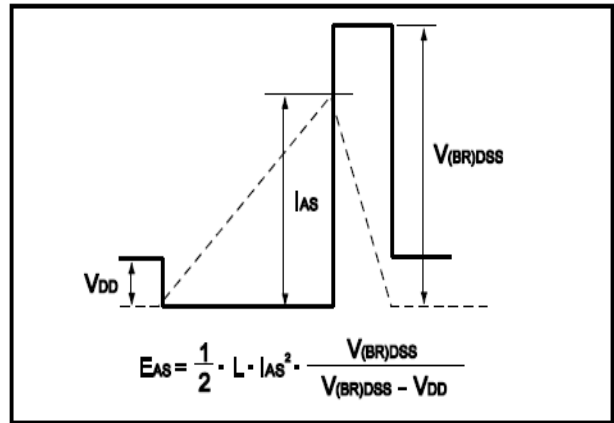


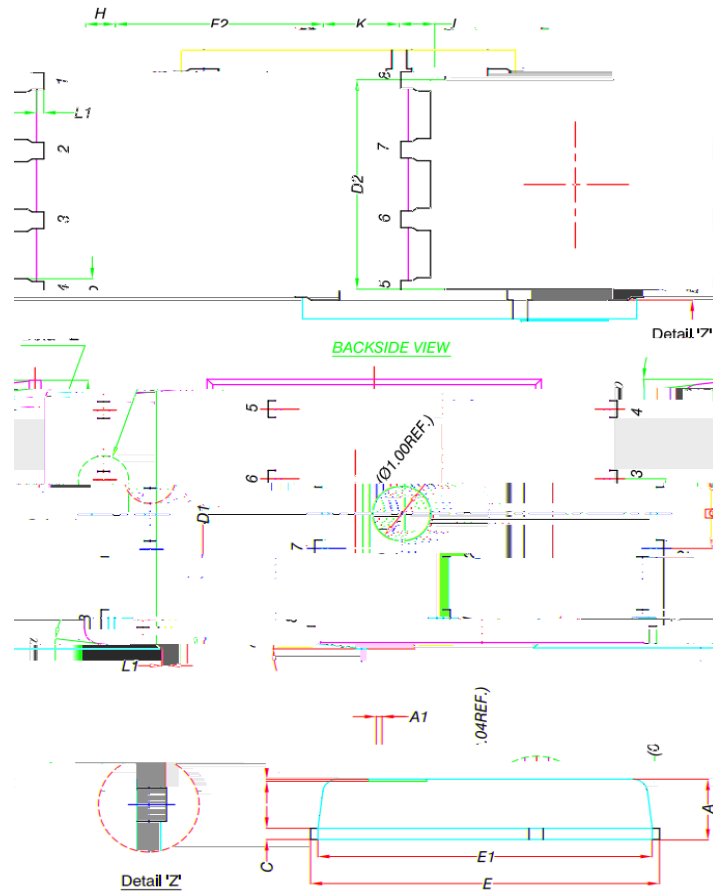
Fig.18 Avalanche Waveform





Dimensions DFN5x6

Unit mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96

